



## A5A:450.XX

### VOLTAGE RATINGS

Part Number	$V_{RRM}, V_R$ (V)		$V_{RSM}, V_R$ (V) Max. non-rep. peak reverse voltage
	$T_J = 0$ to $175^\circ\text{C}$	$T_J = -40$ to $0^\circ\text{C}$	
A5A:450.14	1400	1400	1500
A5A:450.16	1600	1600	1700
A5A:450.18	1800	1800	1900
A5A:450.20	2000	2000	2100
A5A:450.22	2200	2200	2300
A5A:450.24	2400	2400	2500
A5A:450.26	2600	2500	2700

### MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES	
$T_J$ Junction Temperature	-40 to 175	$^\circ\text{C}$	-	
$T_{stg}$ Storage Temperature	-40 to 175	$^\circ\text{C}$	-	
$I_{F(AV)}$ Max. Av. current	360	A	180° half sine wave	
@ Max. $T_C$	125	$^\circ\text{C}$		
$I_{F(RMS)}$ Nom. RMS current	700	A	-	
$I_{FSM}$ Max. Peak non-rep. surge current	5.95	kA	50 Hz half cycle sine wave	Initial $T_J = 175^\circ\text{C}$ , rated $V_{RRM}$ applied after surge.
	6.48		60 Hz half cycle sine wave	
	7.02		50 Hz half cycle sine wave	Initial $T_J = 175^\circ\text{C}$ , no voltage applied after surge.
	7.72		60 Hz half cycle sine wave	
$I^2t$ Max. $I^2t$ capability	161	$\text{kA}^2\text{s}$	$t = 10\text{ms}$	Initial $T_J = 175^\circ\text{C}$ , rated $V_{RRM}$ applied after surge.
	175		$t = 8.3 \text{ ms}$	
	228		$t = 10\text{ms}$	Initial $T_J = 175^\circ\text{C}$ , no voltage applied after surge.
	248		$t = 8.3 \text{ ms}$	
$I^{2t^{1/2}}$ Max. $I^{2t^{1/2}}$ capability	2720	$\text{kA}^2\text{s}^{1/2}$	Initial $T_J = 175^\circ\text{C}$ , no voltage applied after surge. $I^2t$ for time $t_x = I^{2t^{1/2}} * t_x^{1/2}$ . ( $0.1 < t_x < 10\text{ms}$ ).	
F Mounting Force	450	N.m	-	



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### CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
$V_{FM}$ Peak forward voltage	---	1.75	1.99	V	Initial $T_J = 25^\circ\text{C}$ , 50-60Hz half sine, $I_{peak} = 1131\text{A}$ .
$V_{F(TO)1}$ Low-level threshold	---	---	0.83	V	$T_J = 175^\circ\text{C}$
$V_{F(TO)2}$ High-level threshold	---	---	0.864		$\text{Av. power} = V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
$r_F1$ Low-level resistance	---	---	0.876	m	Use low values for $I_{FM} < I_{F(AV)}$
$r_F2$ High-level resistance	---	---	0.658		
$I_{RM}$ Peak reverse current	---	25	40	mA	$T_J = 175^\circ\text{C}$ . Max. Rated $V_{RRM}$
$R_{thJC}$ Thermal resistance, junction-to-case	---	---	0.080	°C/W	DC operation, double side
	---	---	0.092	°C/W	180° sine wave, double side
	---	---	0.094	°C/W	120° rectangular wave, double side
$R_{thCS}$ Thermal resistance, case-to-sink	---	---	0.03	°C/W	Mtg. Surface smooth, flat and greased.
wt Weight	---	57(2.0)	---	g(oz.)	---
Case Style	DO-200AA		JEDEC		---

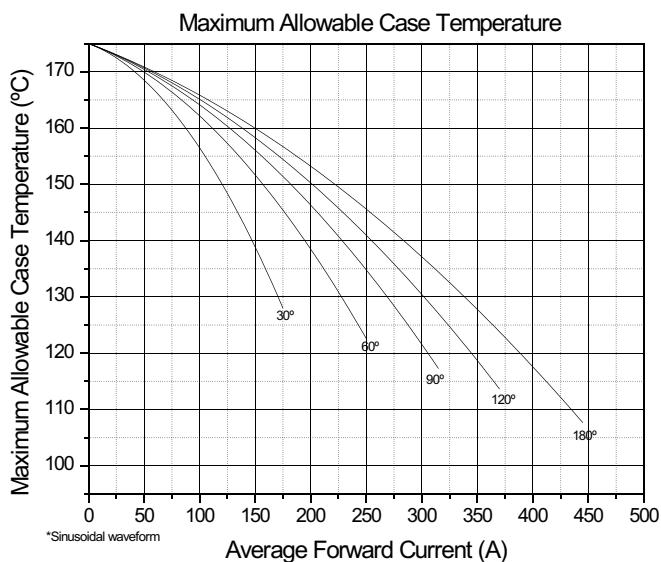


Fig. 1 - Current Ratings Characteristics

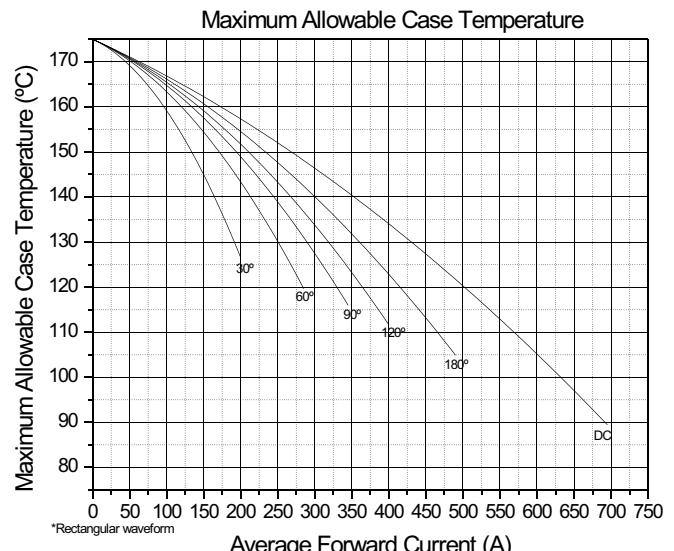
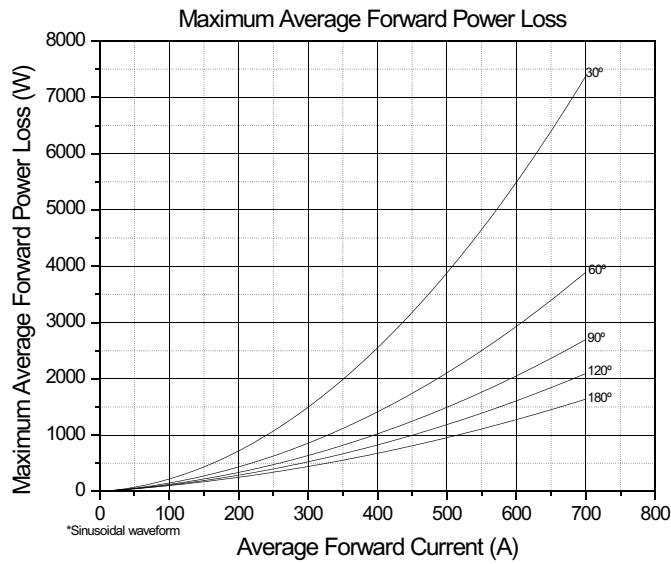


Fig. 2 - Current Ratings Characteristics

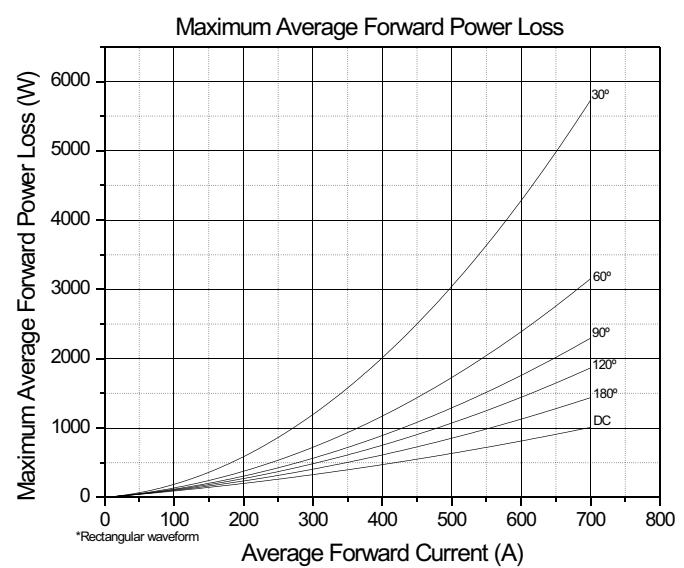


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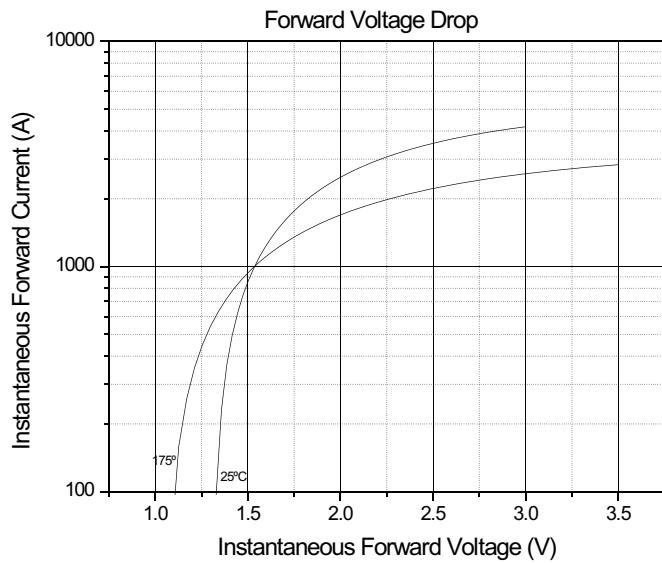
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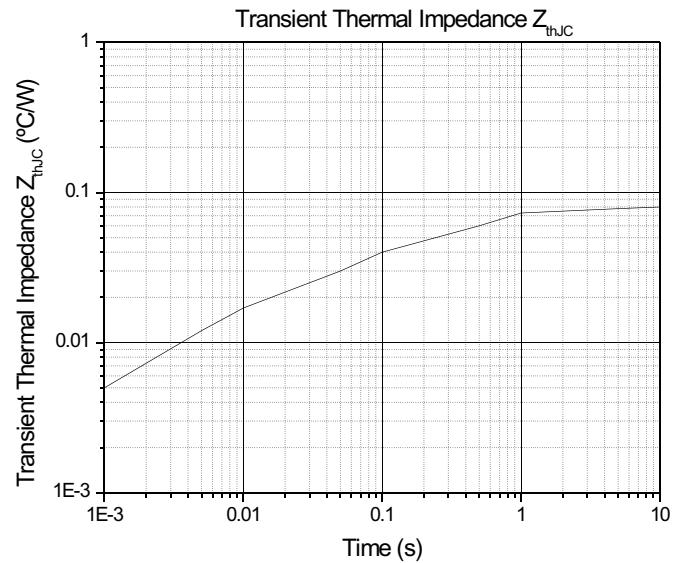
**Fig. 3 - On-State Power Loss Characteristics**



**Fig. 4 - On-State Power Loss Characteristics**



**Fig. 5 - Forward Voltage Drop Characteristics**



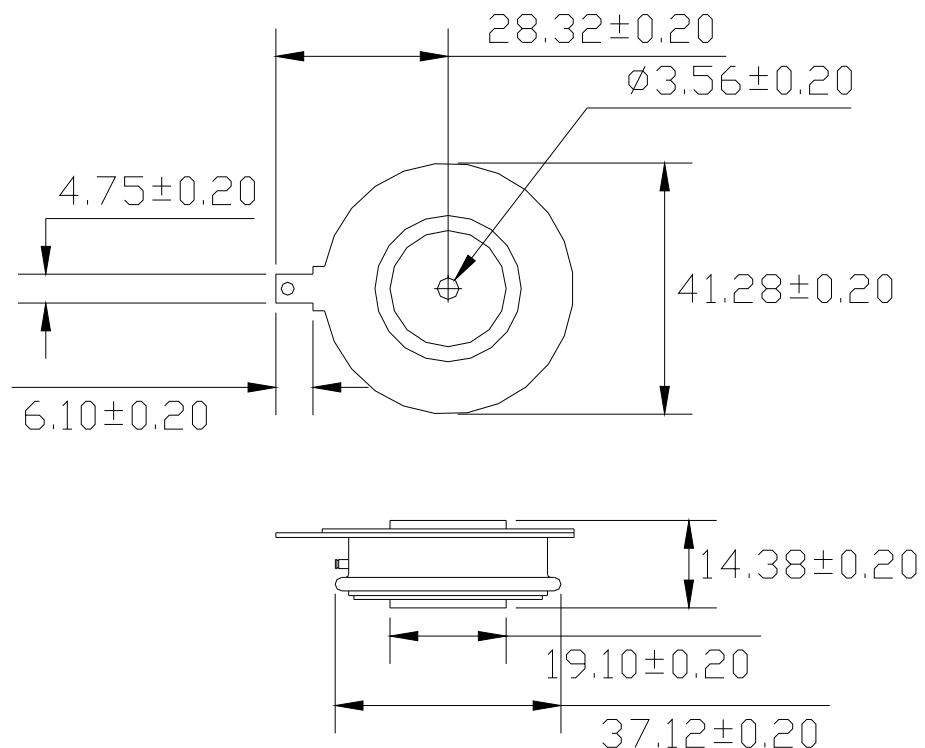
**Fig. 6 - Transient Thermal Impedance Characteristics**



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**TO-200AA**



**Fig. 7 - Outline Characteristics**